

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
30V	12m Ω @ $V_{GS} = 10\text{V}$	10A
	16m Ω @ $V_{GS} = 4.5\text{V}$	8.5A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

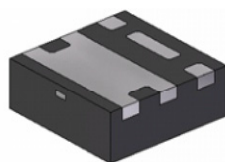
Features and Benefits

- 0.6mm profile – ideal for low profile applications
- PCB footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

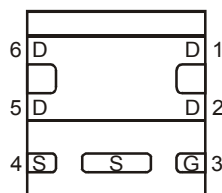
Mechanical Data

- Case: U-DFN2020-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (approximate)

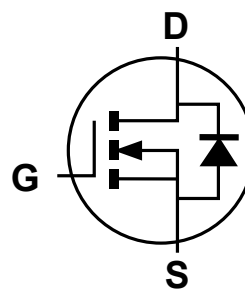
U-DFN2020-6
Type E



Bottom View



Pin Out



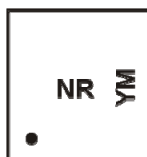
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LFDE-7	U-DFN2020-6 Type E	3,000/Tape & Reel
DMN3016LFDE-13	U-DFN2020-6 Type E	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



NR = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	10 8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	12 9	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2.5	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	90	A
Avalanche Current (Note 7) L = 0.1mH			I _{AR}	22	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH			E _{AR}	24	mJ

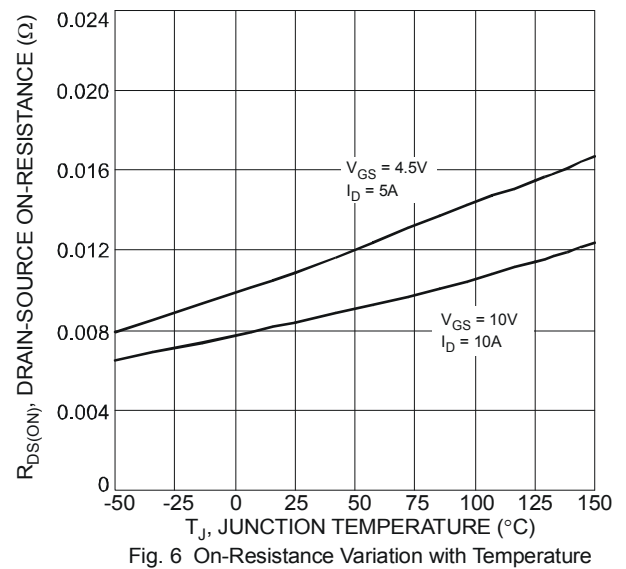
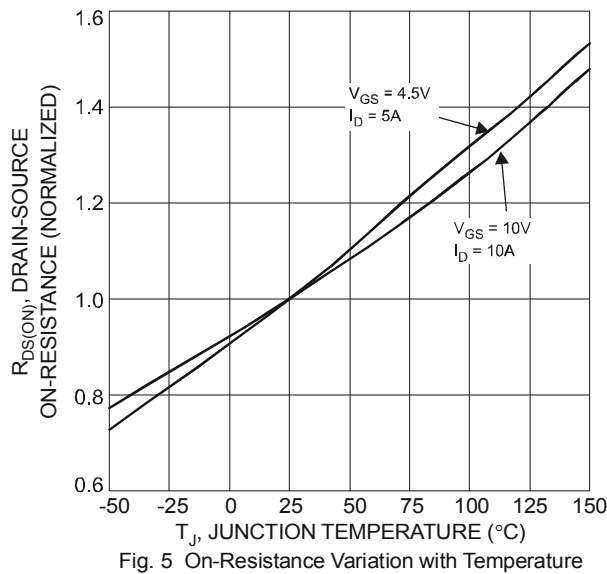
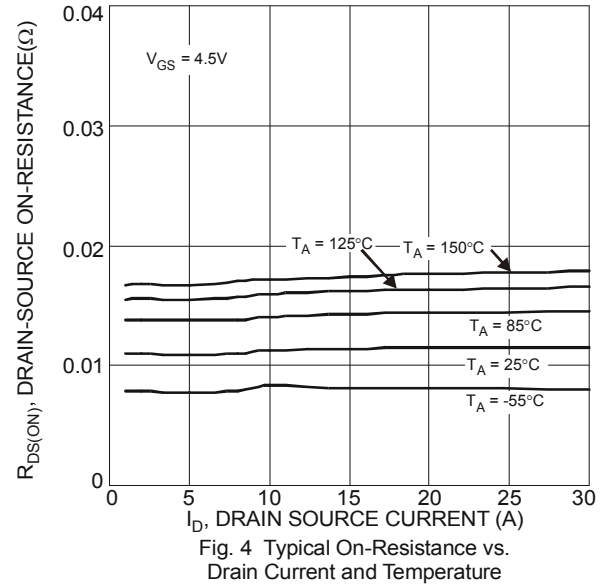
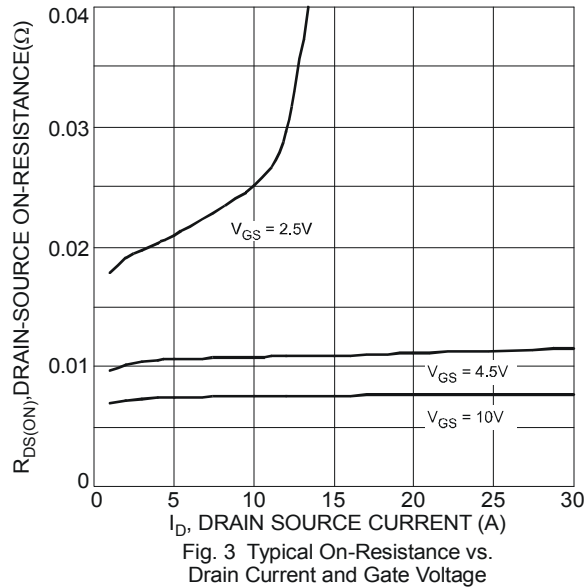
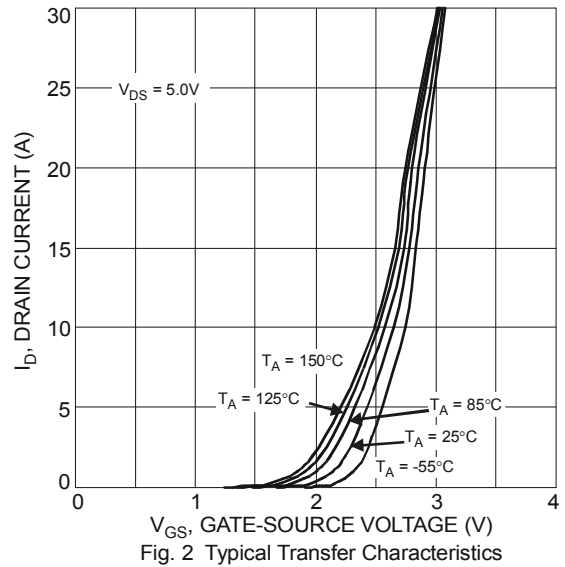
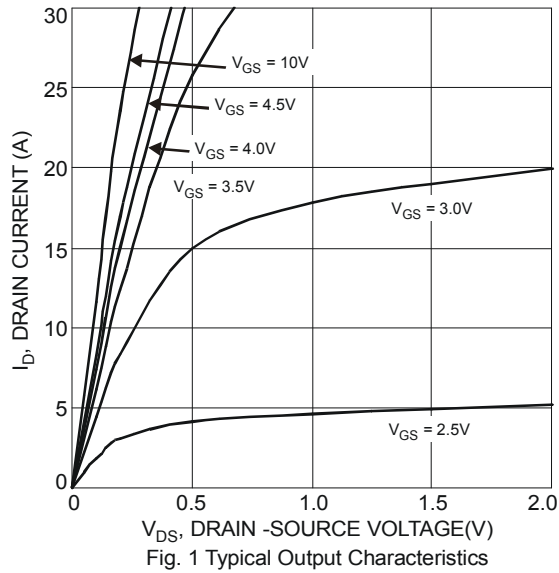
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.73	W
	T _A = +70°C		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	171	°C/W
	t < 10s		121	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.02	W
	T _A = +70°C		1.30	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	62	°C/W
	t < 10s		42	
Thermal Resistance, Junction to Case (Note 6)	Steady state	R _{θJC}	9.3	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.4	-	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	8	12	mΩ	V _{GS} = 10V, I _D = 11A
		-	12	16		V _{GS} = 4.5V, I _D = 9A
Forward Transfer Admittance	Y _{fs}	-	32	-	S	V _{DS} = 5V, I _D = 12A
Diode Forward Voltage	V _{SD}	-	0.70	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	1415	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	119	-		
Reverse Transfer Capacitance	C _{rss}	-	82	-		
Gate resistance	R _g	-	2.6	3.2	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	11.3	-	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	25.1	-		
Gate-Source Charge	Q _{gs}	-	3.5	-		
Gate-Drain Charge	Q _{gd}	-	3.6	-		
Turn-On Delay Time	t _{D(on)}	-	4.8	-	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω,
Turn-On Rise Time	t _r	-	16.5	-		
Turn-Off Delay Time	t _{D(off)}	-	26.1	-		
Turn-Off Fall Time	t _f	-	5.6	-		
Reverse Recovery Time	t _{rr}	-	12.3	-	ns	I _F = 12A, di/dt = 500A/μs
Reverse Recovery Charge	Q _{rr}	-	10.4	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



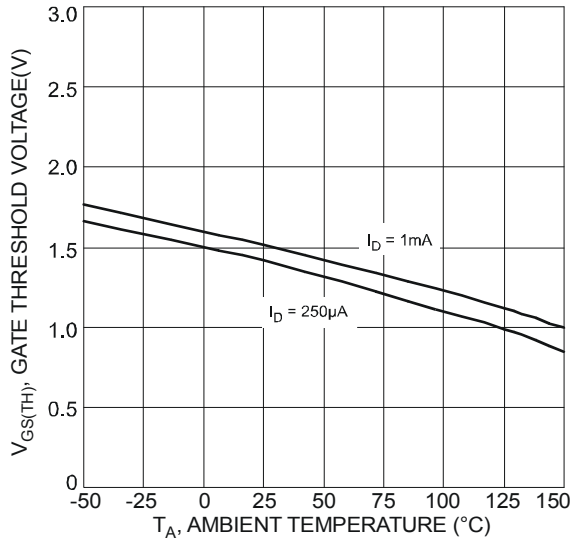


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

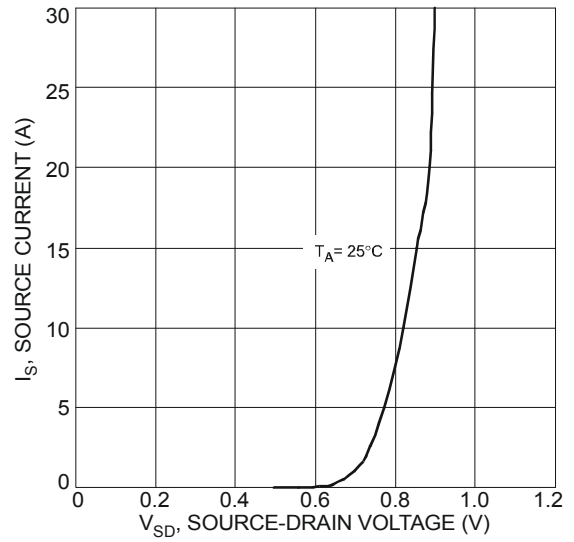


Fig. 8 Diode Forward Voltage vs. Current

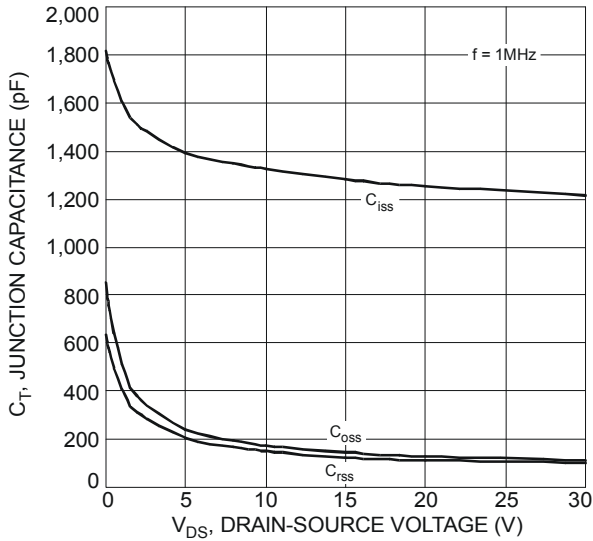


Fig. 9 Typical Junction Capacitance

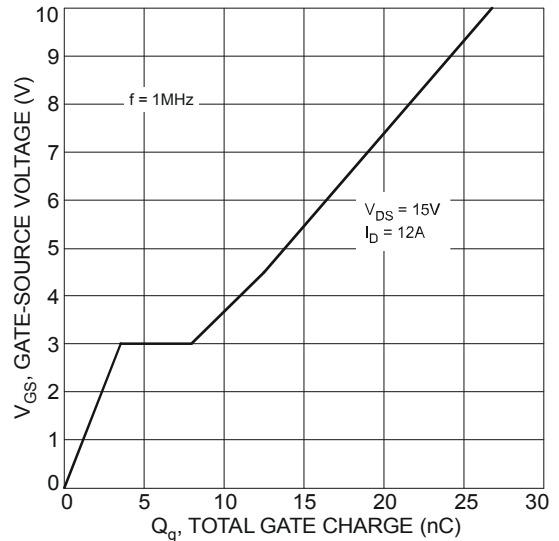


Fig. 10 Gate-Charge Characteristics

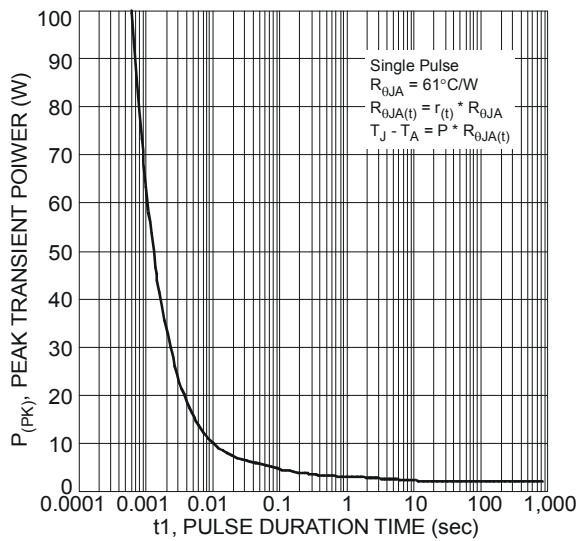
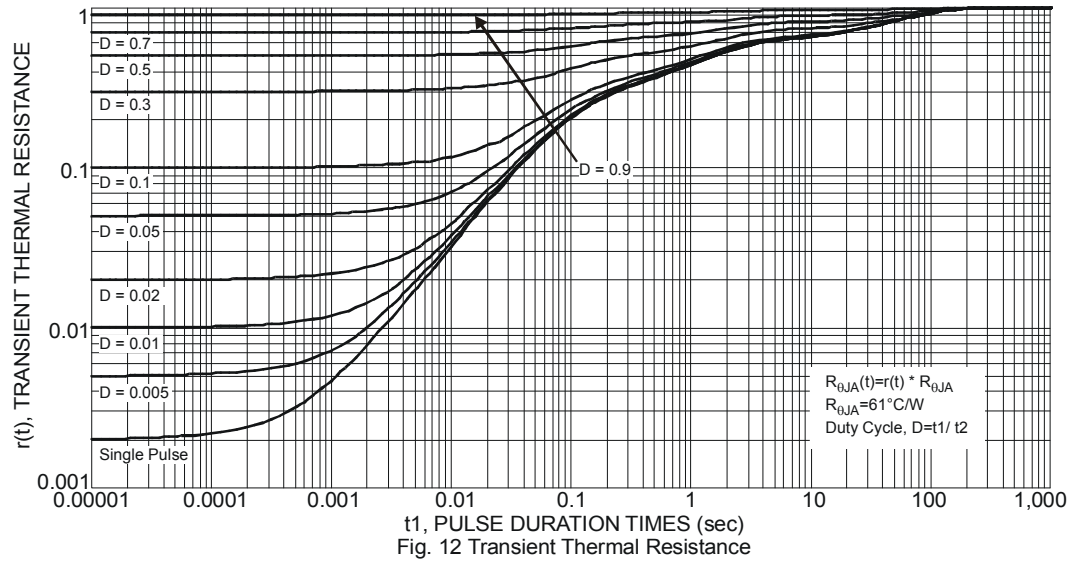
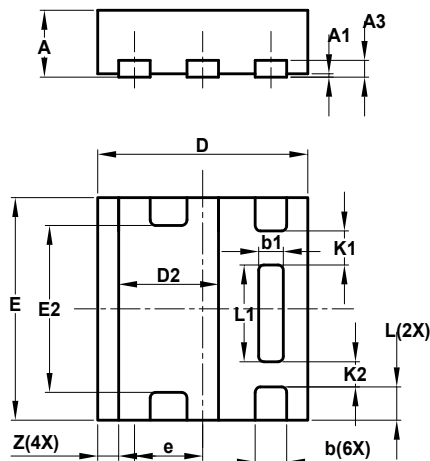


Fig. 11 Single Pulse Maximum Power Dissipation



Package Outline Dimension

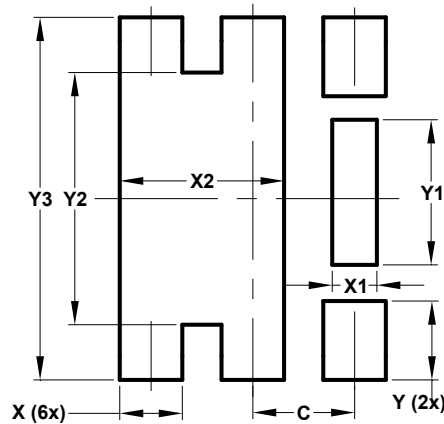
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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